

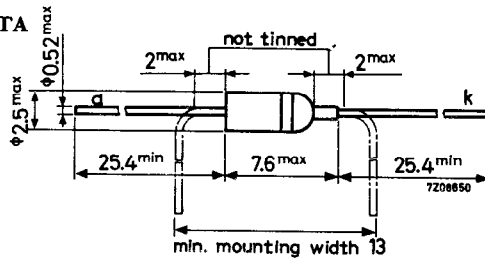
SILICON DIODE

General purpose silicon diode in a subminiature all glass DO-7 envelope.

MECHANICAL DATA

DO-7

Dimensions in mm



The coloured band indicates the cathode side

RATINGS (Limiting values) 1)

Voltage

Continuous reverse voltage V_R max. 60 V

Currents

Forward current (d.c.) I_F max. 90 mA

Repetitive peak forward current I_{FRM} max. 100 mA

Non repetitive peak forward current ($t \leq 1$ s) I_{FSM} max. 200 mA

Temperatures

Storage temperature T_{stg} -55 to +90 °C

Junction temperature T_j max. 90 °C

THERMAL RESISTANCE

From junction to ambient in free air $R_{th\ j-a} = 0.4$ °C/mW

CHARACTERISTICS

Forward voltage

	$T_{amb} = 25$ °C	$T_{amb} = 60$ °C
$I_F = 0.1$ mA	V_F typ. 0.55 < 0.75	typ. 0.5 V V
$I_F = 1.0$ mA	V_F typ. 0.65 0.5 to 1.0	typ. 0.6 V 0.4 to 0.9 V
$I_F = 30$ mA	V_F typ. 0.9 < 1.5	typ. 0.85 V < 1.5 V

Reverse current

	$T_{amb} = 60$ °C	$T_{amb} = 75$ °C
$V_R = 10$ V	I_R typ. 5.0	< 10 μA
$V_R = 60$ V	I_R typ. 10	< 20 μA

1) Limiting values according to the Absolute Maximum System as defined in IEC publication 134.